FS5N10S

N-Channel SMD MOSFET

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
100V	125mΩ@10V	5A
	145mΩ@4.5V	

Feature

- Advanced trench process technology
- High density cell design for ultra low on-resistance

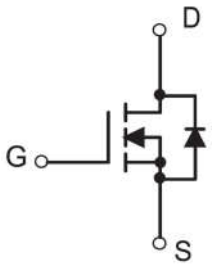
Application

- Load Switch for Portable Devices
- DC/DC Converter

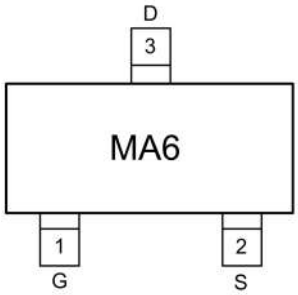
Package

SOT-23

Circuit diagram



Marking



Absolute maximum ratings (Ta=25℃ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current	I_D	5	A
Pulsed Drain Current	I_{DM}	16	A
Power Dissipation	P_D	3.1	W
Junction Temperature	T_J	150	℃
Storage Temperature	T_{STG}	-55 ~ +150	℃

Electrical characteristics (T_A=25 °C, unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D =250μA	100			V
Zero gate voltage drain current	I_{DSS}	V_{DS} =80V,V_{GS} = 0V			1	μA
Gate-body leakage current	I_{GSS}	V_{GS} =±20V, V_{DS} = 0V			±100	nA
Gate threshold voltage	$V_{GS(th)}$	V_{DS} =V_{GS}, I_D =250μA	1.2	1.7	2.5	V
Drain-source on-resistance[1]	$R_{DS(on)}$	V_{GS} =10V, I_D =4A		105	125	mΩ
		V_{GS} =4.5V, I_D =2A		120	145	
Dynamic characteristics[2]						
Input Capacitance	C_{iss}	V_{DS} =50V,V_{GS} =0V,f =1MHz		182		pF
Output Capacitance	C_{oss}			30		
Reverse Transfer Capacitance	C_{rss}			3.6		
Total Gate Charge	Q_g	V_{DS} =30V,V_{GS} =10V, I_D =4A		3.6		nC
Gate-Source Charge	Q_{gs}			0.76		
Gate-Drain Charge	Q_{gd}			0.71		
Turn-on delay time	$t_{d(on)}$	V_{DD}=30V, V_{GS} =10V, I_D =1A R_G=3.3Ω		11		nS
Turn-on rise time	t_r			6		
Turn-off delay time	$t_{d(off)}$			30		
Turn-off fall time	t_f			4		
Source-Drain Diode characteristics						
Diode Forward voltage	V_{SD}	V_{GS} =0V, I_S=2A			1.2	V

Notes:

1) Pulse Test: Pulse Width < 300μs, Duty Cycle ≤2%.

2) Guaranteed by design, not subject to production testing.

Typical Characteristics

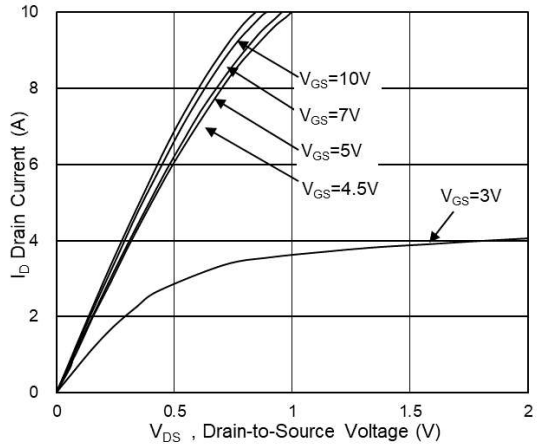


Fig.1 Typical Output Characteristics

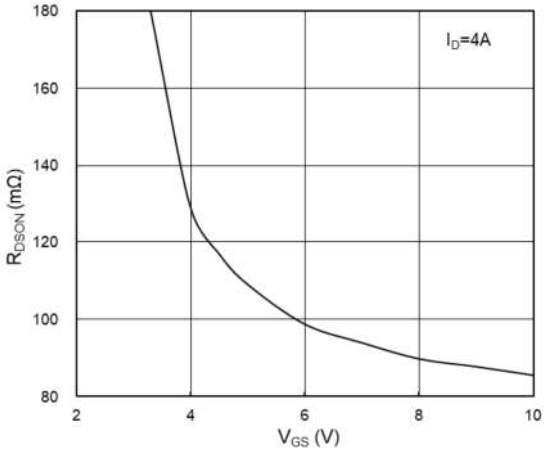


Fig.2 On-Resistance vs G-S Voltage

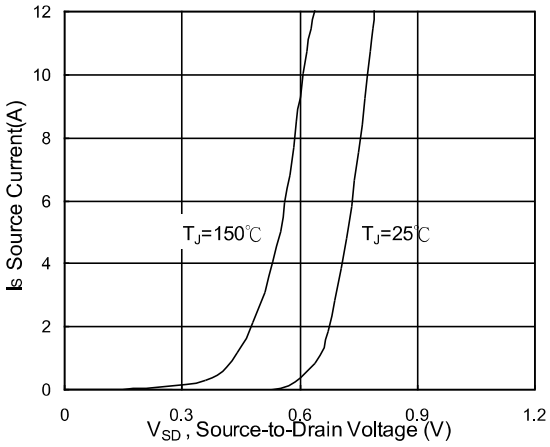


Fig.3 Source Drain Forward Characteristics

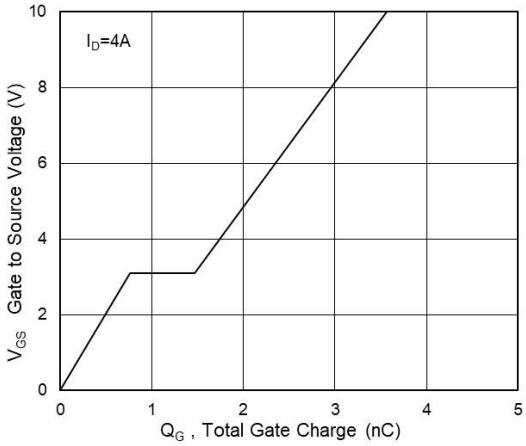


Fig.4 Gate-Charge Characteristics

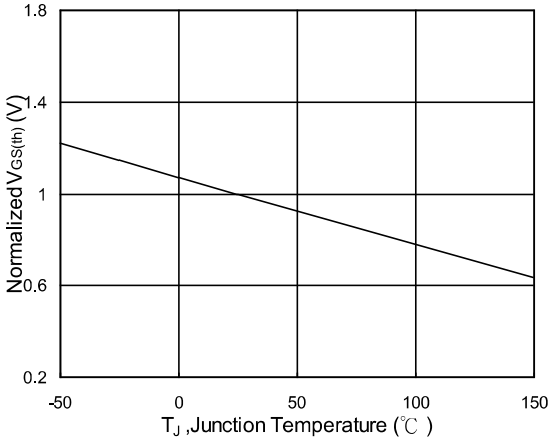


Fig.5 Normalized $V_{GS(th)}$ vs T_J

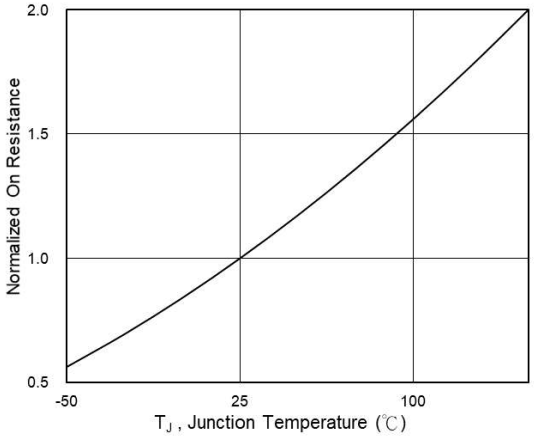
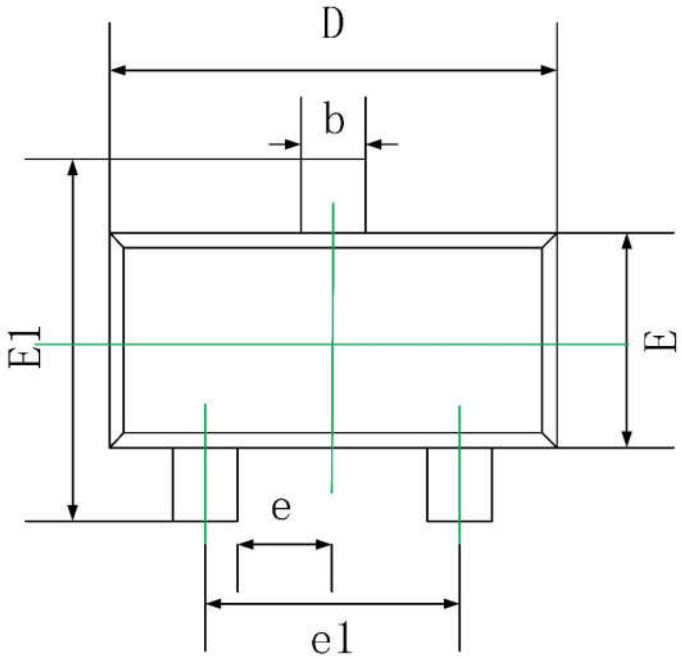
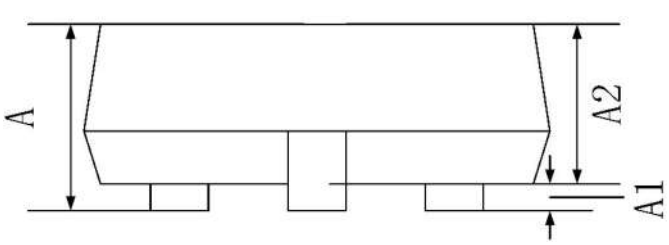
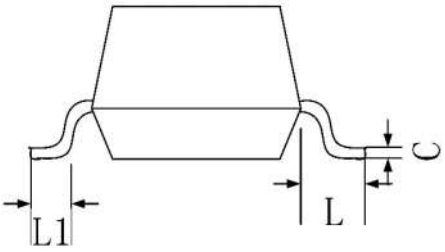


Fig.6 Normalized R_{DSON} vs T_J

SOT-23 Package Information







Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP.		0.037 TYP.	
e1	1.800	2.000	0.071	0.079
L	0.550 REF.		0.022 REF.	
L1	0.300	0.500	0.012	0.020

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